

**AMENDMENT TO THE SPECIFICATION:**

Please replace paragraph [0009] of the specification with the following amended paragraph:

[0009] The present invention further provides a film-forming method of forming a titanium nitride film on a substrate to be processed in a chamber through reaction of titanium tetrachloride and ammonia, the method including: a first step of supplying titanium tetrachloride and ammonia into the chamber with flow rate ratio of the ~~titanium tetrachloride to the ammonia~~ to the titanium tetrachloride being a first flow rate ratio, while pressure in the chamber being maintained within a range of  $3.94 \times 10^{-4}$  to  $1.32 \times 10^{-2}$  atm, thereby forming a first titanium nitride layer on the substrate; a second step of supplying titanium tetrachloride and ammonia into the chamber with flow rate ratio of the ~~titanium tetrachloride to the ammonia~~ to the titanium tetrachloride being a second flow rate ratio smaller than the first flow rate ratio, while pressure in the chamber being maintained within a range of  $3.94 \times 10^{-4}$  to  $1.32 \times 10^{-2}$  atm, thereby forming a second titanium nitride layer on the first titanium nitride layer.